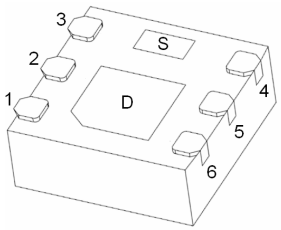
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

DFNWB2*2-6L-J Plastic-Encapsulate MOSFETS

CJM1206 P-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
-12V	45mΩ@-4.5V	-6A
	60mΩ@-2.5V	
	90mΩ@-1.8V	

DFNWB2*2-6L-J



1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

DESCRIPTION

The CJM1206 uses advanced trench technology to provide excellent $R_{DS(on)}$, low gate charge and operation with low gate voltage.

This device is suitable for use as a load switching application and a wide variety of other applications.

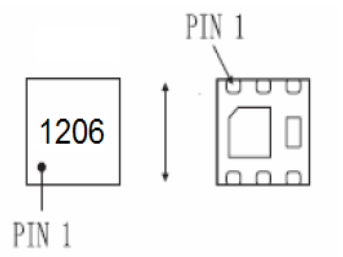
FEATURES

- Advanced trench MOSFET process technology
- Ultra low on-resistance with low gate charge

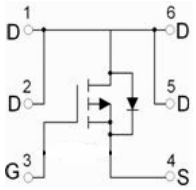
APPLICATIONS

- PWM application
- Load switch
- Battery charge in cellular handset

MARKING



Equivalent Circuit



Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	±8	
Drain Current-Continuous	I_D	-6	A
Drain Current-Pulsed	I_{DM}*	-20	
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	℃/W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{STG}	-55 ~+150	

*Repetitive rating：Pluse width limited by junction temperature.

MOSFET ELECTRICAL CHARACTERISTICS

T_a=25℃ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-12			V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.5		-0.9	
Gate-source leakage	I_{GSS}	V_{DS} =0V, V_{GS} =±8V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} =-8V, V_{GS} =0V			-1	μA
Drain-source on-state[a] resistance	$R_{DS(on)}$	V_{GS} =-4.5V, I_D =-3.5A		30	45	mΩ
		V_{GS} =-2.5V, I_D =-3A		40	60	
		V_{GS} =-1.8V,I_D=-2.0A		60	90	
Forward transconductance[a]	g_{fs}	V_{DS} =-5V, I_D =-4.1A	6			S
Dynamic						
Input capacitance[b,c]	C_{iss}	V_{DS} =-4V,V_{GS} =0V,f =1MHz		740		pF
Output capacitance[b,c]	C_{oss}			290		
Reverse transfer capacitance[b,c]	C_{rss}			190		
Total gate charge[b]	Q_g	V_{DS} =-4V,V_{GS} =-4.5V, I_D =-4.1A		7.8	15	nC
		V_{DS} =-4V,V_{GS} =-2.5V, I_D =-4.1A		4.5	9	
Gate-source charge[b]	Q_{gs}			1.2		
Gate-drain charge[b]	Q_{gd}			1.6		
Gate resistance[b,c]	R_g	f =1MHz	1.4	7	14	Ω
Turn-on delay time[b,c]	$t_{d(on)}$	V_{DD}=-4V, R_L=1.2Ω, I_D ≈-3.3A, V_{GEN}=-4.5V,Rg=1Ω		13	20	ns
Rise time[b,c]	t_r			35	53	
Turn-off Delay time[b,c]	$t_{d(off)}$			32	48	
Fall time[b,c]	t_f			10	20	
Turn-on delay time[b,c]	$t_{d(on)}$	V_{DD}=-4V, R_L=1.2Ω, I_D ≈-3.3A, V_{GEN}=-8V,Rg=1Ω		5	10	
Rise time[b,c]	t_r			11	17	
Turn-off delay time[b,c]	$t_{d(off)}$			22	33	
Fall time[b,c]	t_f			16	24	
Drain-source body diode characteristics						
Continuous source-drain diode current	I_S				-6	A
Pulse diode forward current[a]	I_{SM}				-20	
Body ciode voltage	V_{SD}	I_F=-3.3A			-1.2	V

Note :

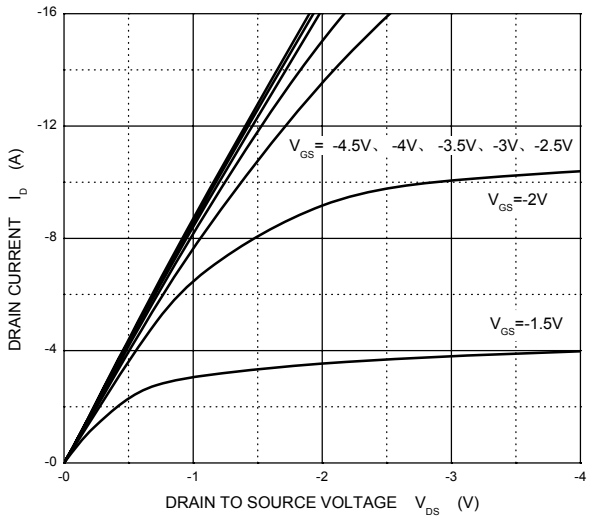
a. Pulse Test ; Pulse Width ≤300μs, Duty Cycle ≤2%.

b. Guaranteed by design, not subject to production testing.

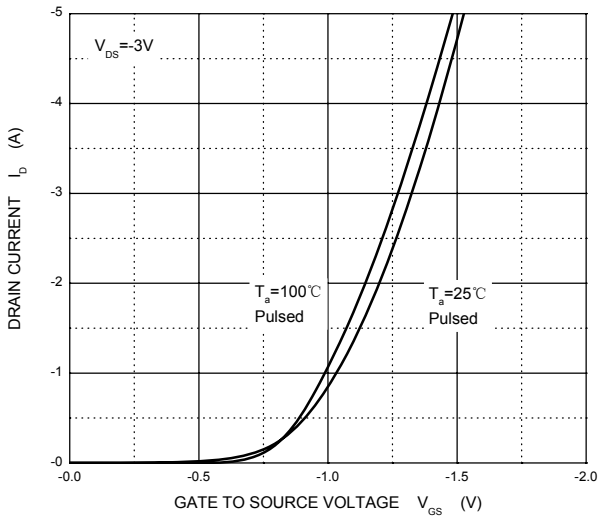
c. These parameters have no way to verify.

Typical Characteristics

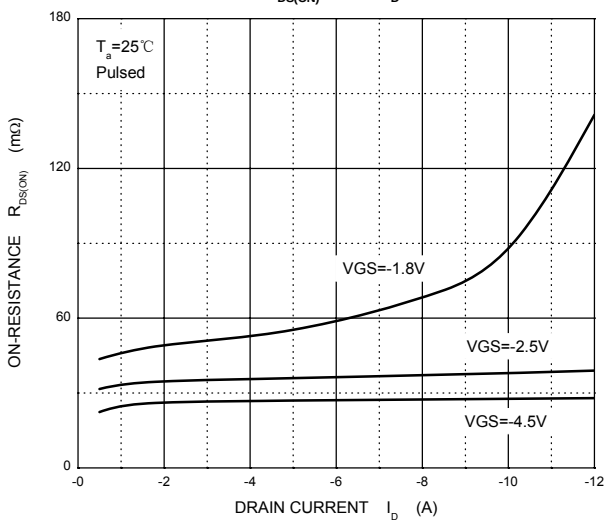
Output Characteristics



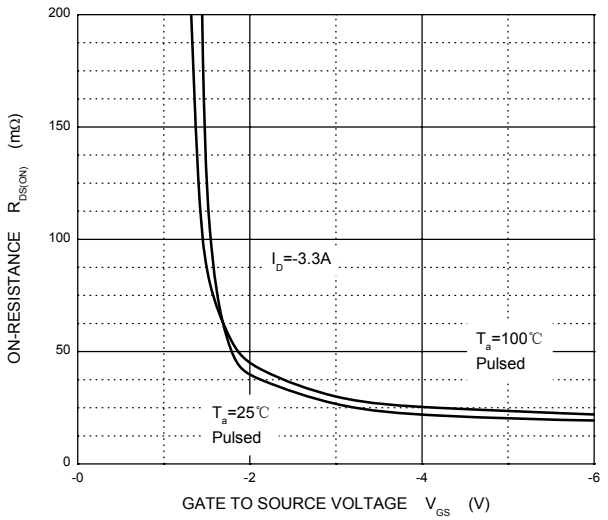
Transfer Characteristics



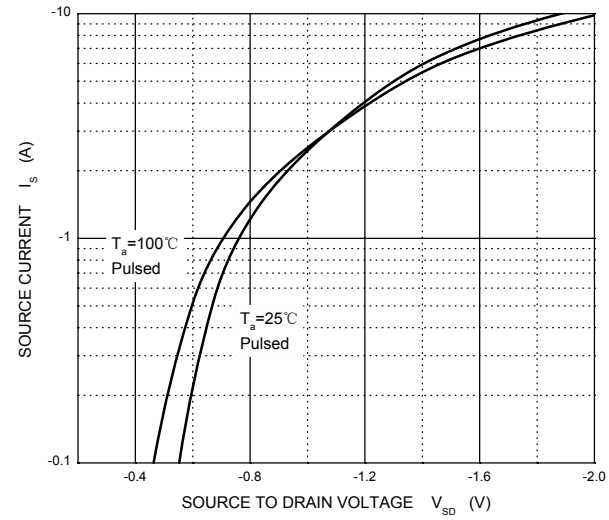
$R_{DS(ON)}$ —— I_D



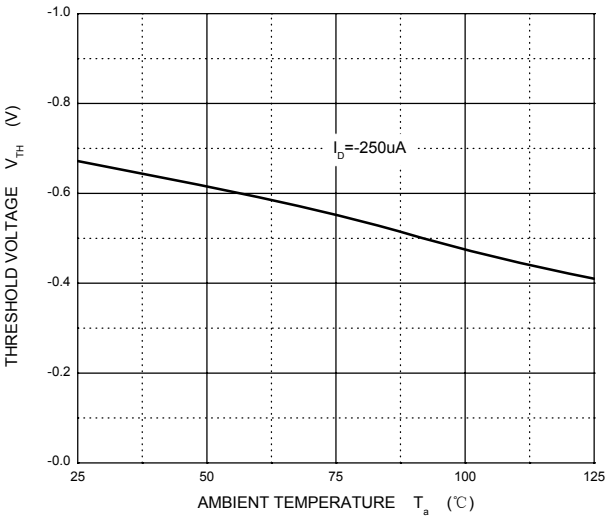
$R_{DS(ON)}$ —— V_{GS}



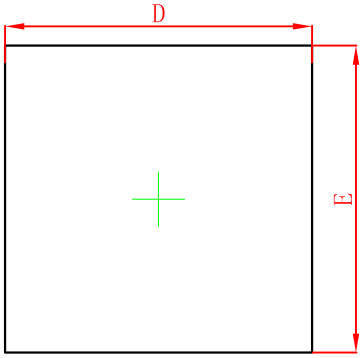
I_S —— V_{SD}

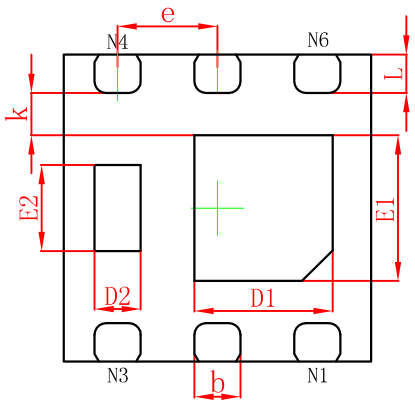


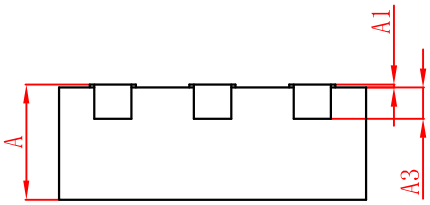
Threshold Voltage



DFNWB2X2-6L-J Package Outline Dimensions

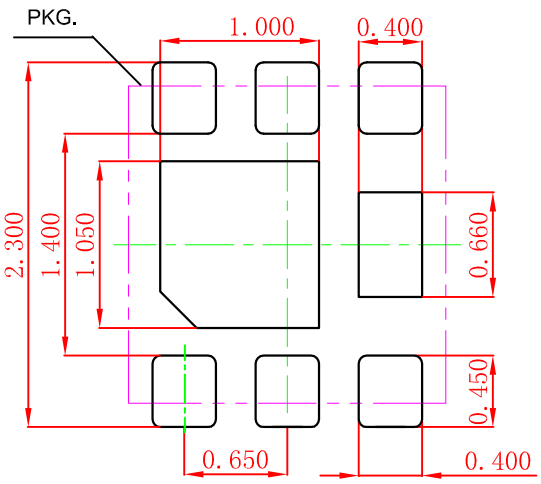






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.032
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

DFNWB2X2-6L-J Suggested Pad Layout

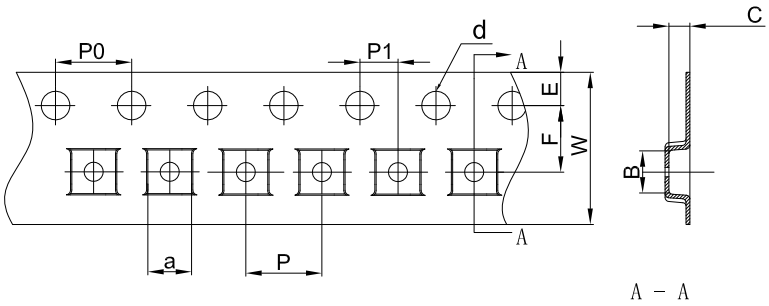


Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.050mm.
3.The pad layout is for reference purposes only.

NOTICE

JCET reserve the right to make modifications,enhancements, improvements, corrections or other changes without further notice to any product herein.JCET does not assume any liability arising out of the application or use of any product described herein.

DFNWB2×2-6L Embossed Carrier Tape

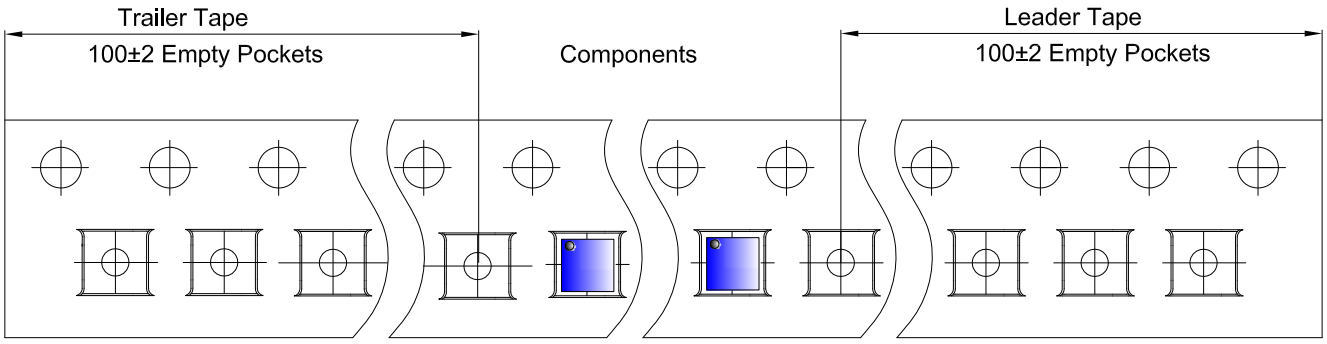


Packaging Description:

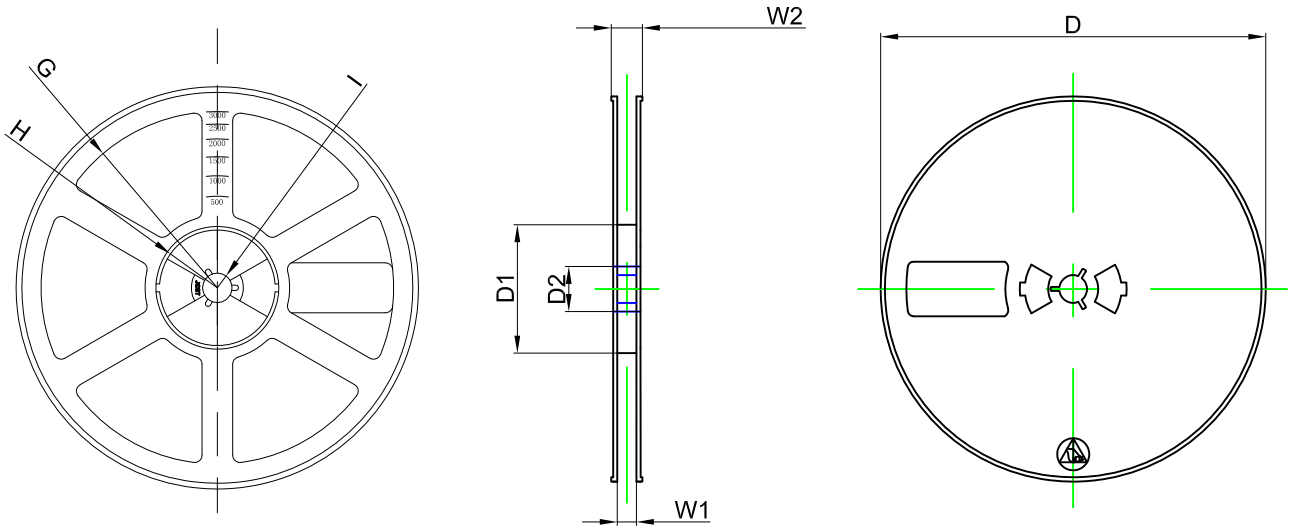
DFNWB2×2-6L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 18.0cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
DFNWB2×2-6L	2.30	2.30	1.10	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

DFNWB2×2-6L Tape Leader and Trailer



DFNWB2×2-6L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø180.00	60.00	13.00	R78.00	R25.60	R6.50	9.50	13.10

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	